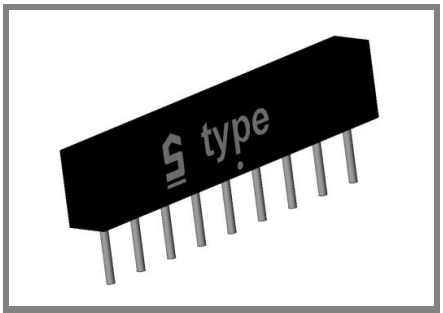
DAN 801, DAP 801 (200mW) ...



Diode arrays

Silicon rectifiers arrays

DAN 801, DAP 801 (200mW)

Forward Current: 0,1 A

Reverse Voltage: 80 to / V

Publish Data

Features

Mechanical Data

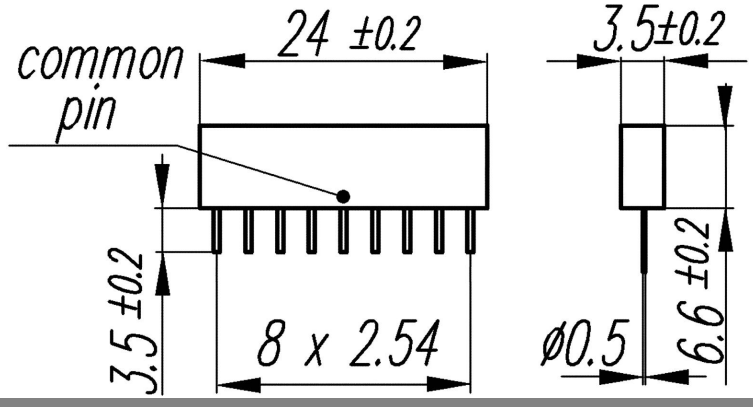
- 9 Pin - plastic case
- Terminals: plated terminals solderable per IEC 68-2-20
- Mounting position : any
- Weigh approx. 0,6 g
- Standard packing : bulk
- DAP 801 - common anodes
- DAN 801- common cathodes
- [1] Valid for one branch; per diode for simultaneous operation I_{FAV} = 25 mA
- [2] I_F = 10mA, T_A = 25°C

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time I_F = 10 m A, I_R = 10 m A, I_{RR} = 1 m A t_{rr} ns	Max. forward voltage V_F [2]
DAN 803	80	80	4	1,0
DAP 803	80	80	4	1,0

Absolute Maximum Ratings		T_c = 25°C unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
I_{FAV}	Max. averaged fwd. current, R-load, T_A = 25 °C [1]	0,1	A
I_{FRM}	Repetitive peak forward current f > 15 Hz [1]	0,2	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave [3]	0,5	A
i²t	Rating for fusing, t < 10 ms [3]	0,0012	A²s
R_{thA}	Max. thermal resistance junction to ambient [1]	85	K/W
R_{thT}	Max. thermal resistance junction to terminals [1]	/	K/W
T_j	Operating junction temperature	-50 ... +150	°C
T_s	Storage temperature	-50 ... +150	°C

Characteristics		T_c = 25°C unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
I_R	Maximum leakage current, T_j = 25 °C; V_R = V_{RRM}	<25 (note : V_R = 20 V)	nA
	T_j = °C; V_R = V_{RRM}		
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)	/	pF
Q_{rr}	Reverse recovery charge (U_R = V; I_F = A; dI_F/dt = A/ms)	/	µC
E_{RSM}	Non repetitive peak reverse avalanche energy (I_R = mA; T_j = °C; inductive load switched off)		mJ

Dimensions in mm



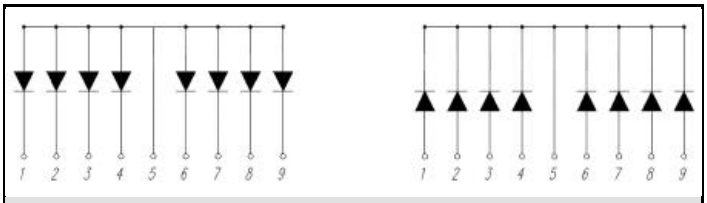


Fig. 1 : DAP 801 (Com.anodes) DAP 803 (Com. cathodes)

